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[SI3457BDV-T1-E3](#)

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Si3457BDV
 Vishay Siliconix

P-Channel 30-V (D-S) MOSFET

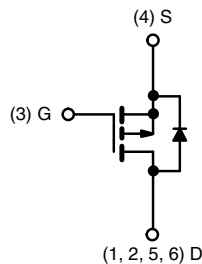
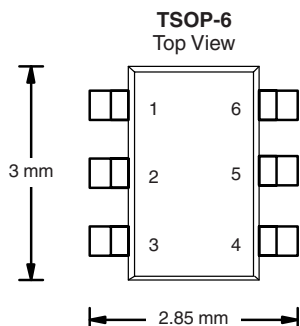
PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
- 30	0.054 at V _{GS} = - 10 V	- 5.0
	0.100 at V _{GS} = - 4.5 V	- 3.7

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs



RoHS
 COMPLIANT
 HALOGEN
FREE
 Available



P-Channel MOSFET

Ordering Information: Si3457BDV-T1-E3 (Lead (Pb)-free)
 Si3457BDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code: 7Bxxx

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted					
Parameter	Symbol	5 s	Steady State	Unit	
Drain-Source Voltage	V _{DS}	- 30		V	
Gate-Source Voltage	V _{GS}	± 20			
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 5.0	- 3.7	A
		T _A = 70 °C	- 4.0	- 3.0	
Pulsed Drain Current	I _{DM}	- 20			
Continuous Source Current (Diode Conduction) ^a	I _S	- 1.7	- 0.95		
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2.0	1.14	W
		T _A = 70 °C	1.3	0.73	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	53	62.5	°C/W
		Steady State	90	110	
Maximum Junction-to-Foot (Drain)	R _{thJF}	25	36		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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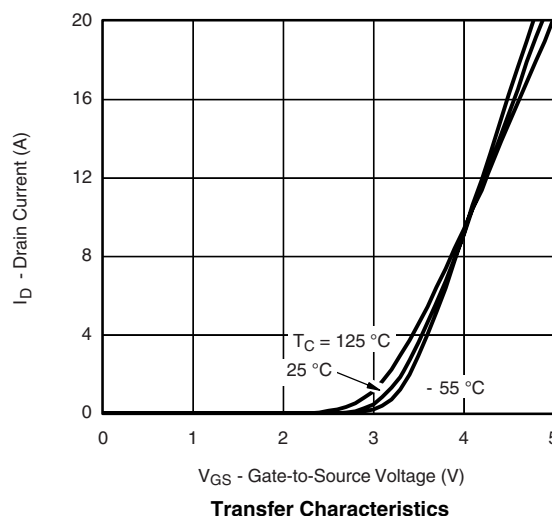
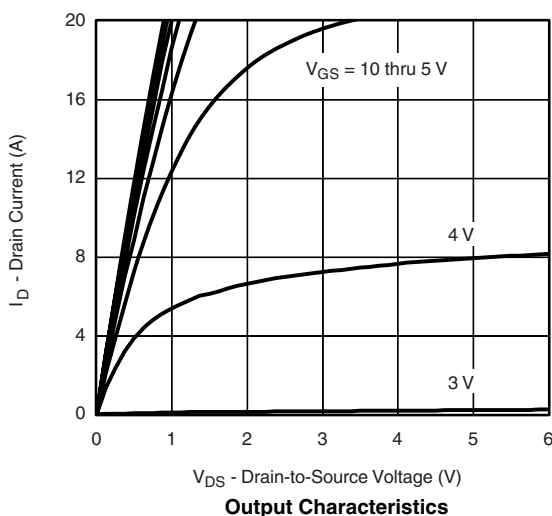
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	-20			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -5.0\text{ A}$		0.044	0.054	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -3.7\text{ A}$		0.082	0.100	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -5.0\text{ A}$		10		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -5.0\text{ A}$		12.5	19	nC
Gate-Source Charge	Q_{gs}			2.1		
Gate-Drain Charge	Q_{gd}			3.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$		7	15	ns
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			30	45	
Fall Time	t_f			22	35	
Source-Drain Reverse Recovery Time	t_{rr}		$I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		25	

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

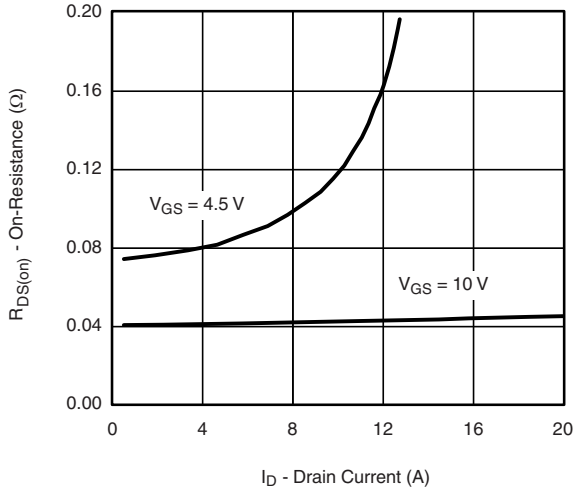
TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted



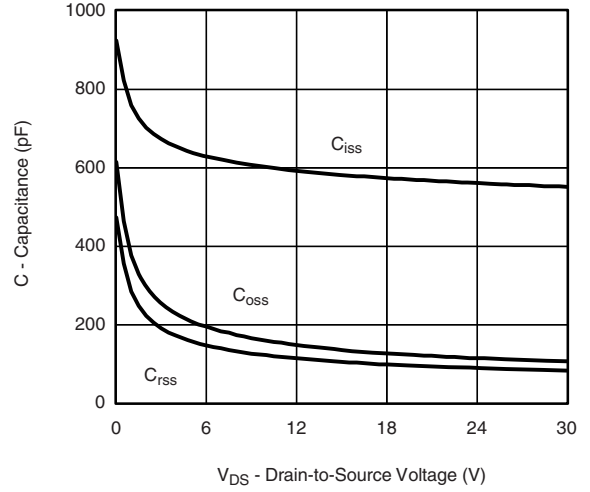


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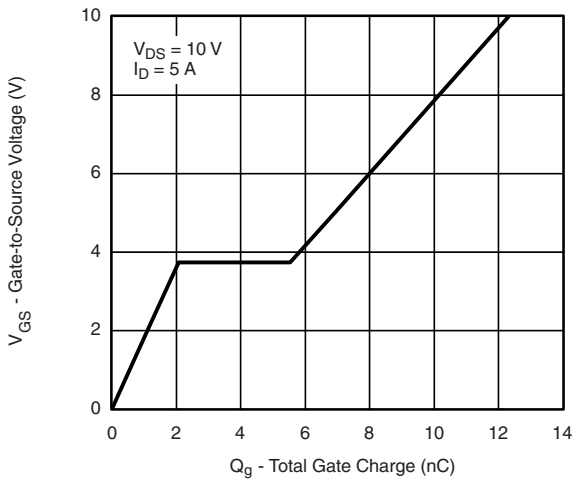
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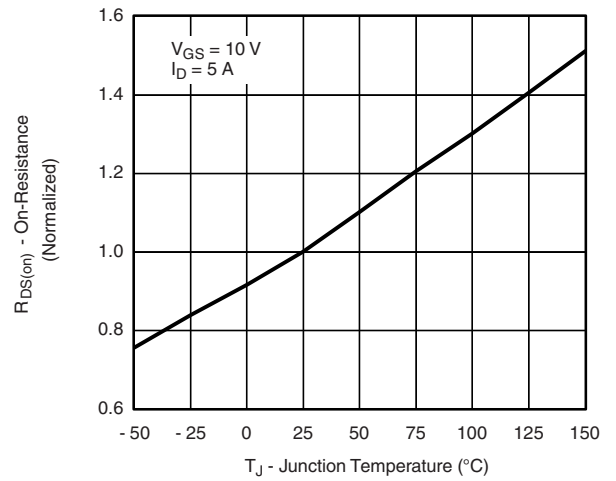
On-Resistance vs. Drain Current



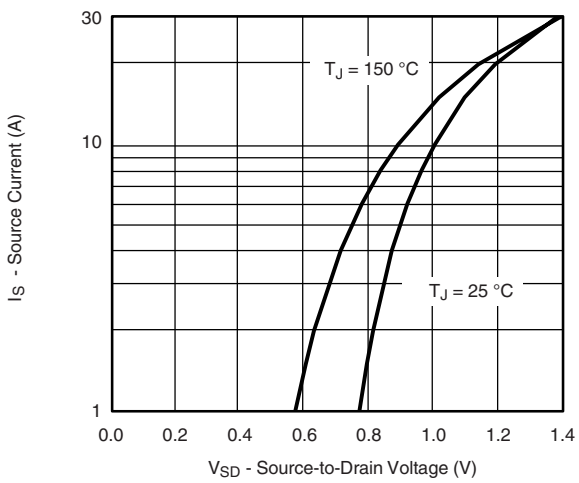
Capacitance



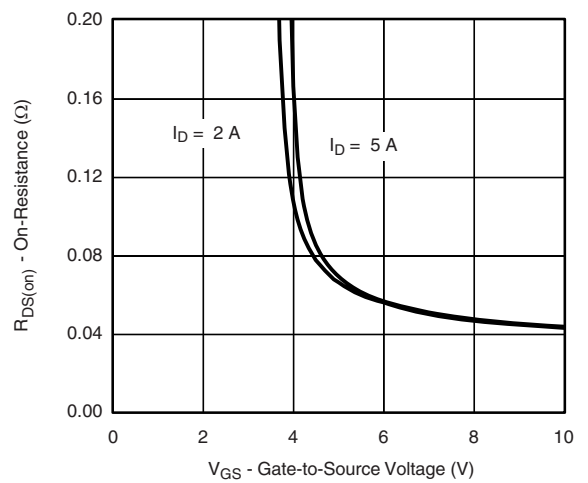
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

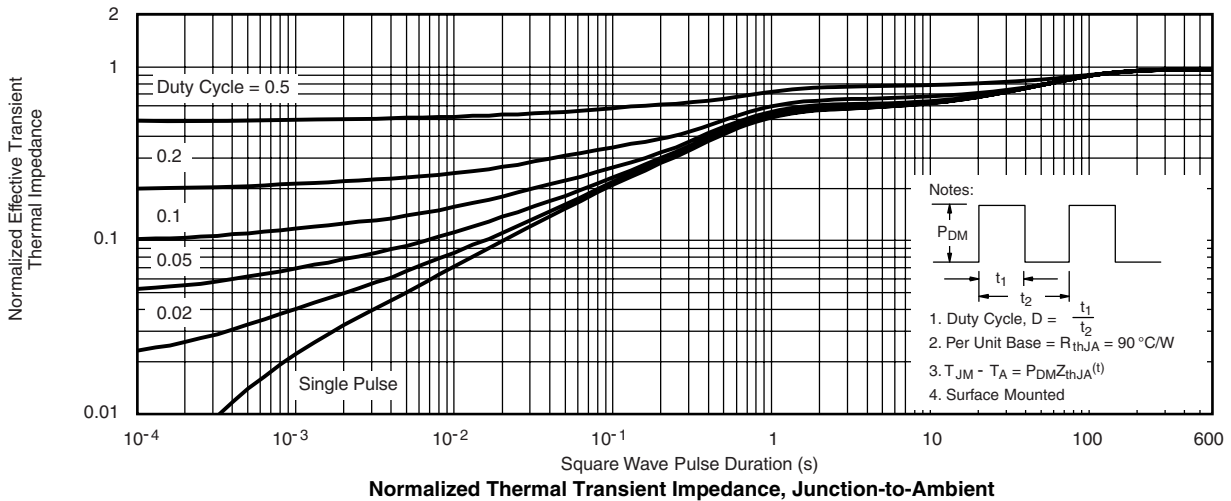
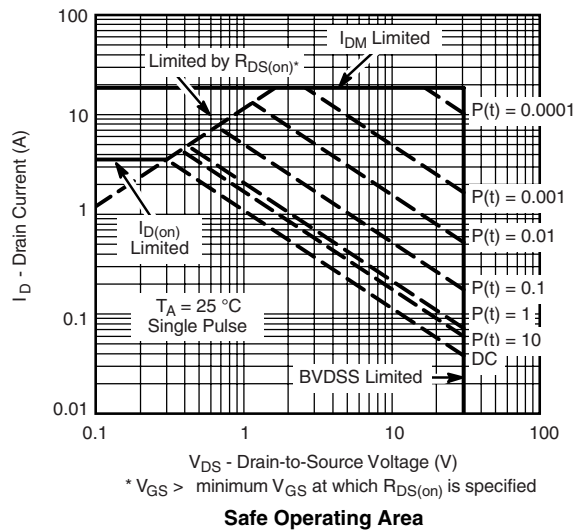
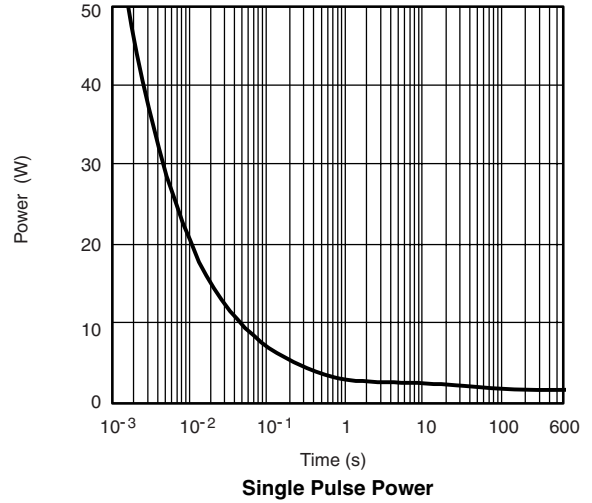
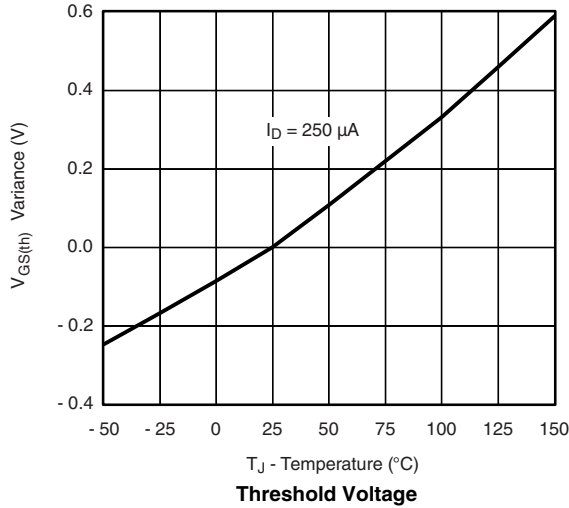


On-Resistance vs. Gate-to-Source Voltage

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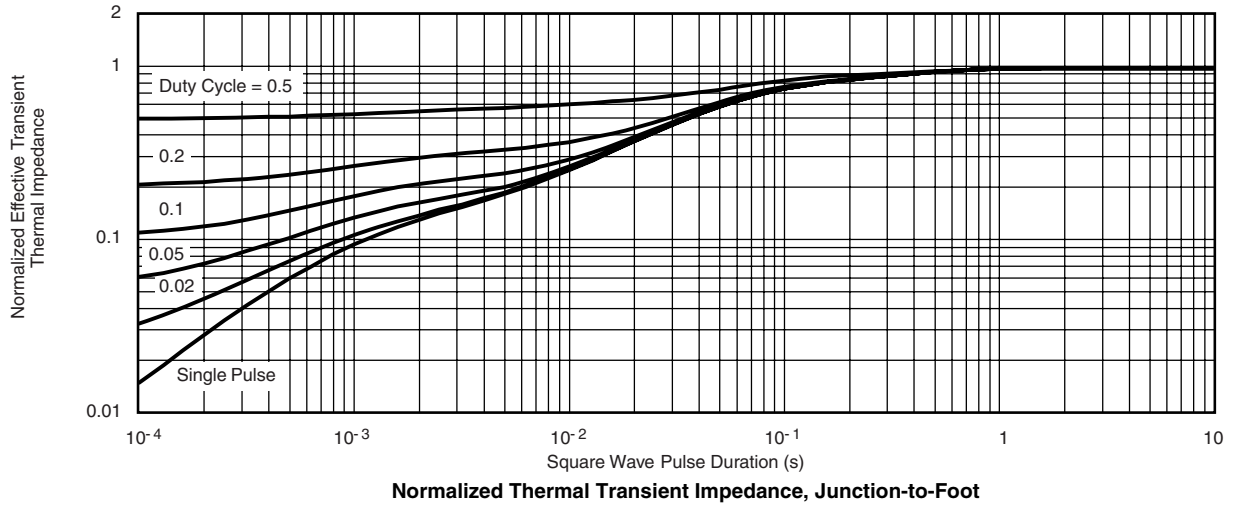
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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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